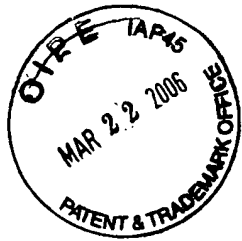


IFW



Docket No.: M4065.0439/P439
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Joseph E. Geusic et al.

Application No.: 09/855,532

Confirmation No.: 9772

Filed: May 16, 2001

Art Unit: 2828

For: METHOD OF FORMING MIRRORS BY
SURFACE TRANSFORMATION OF
EMPTY SPACES IN SOLID STATE
MATERIALS AND STRUCTURES
THEREON (AS AMENDED)

Examiner: A. Rodriguez

INFORMATION DISCLOSURE STATEMENT (IDS)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Pursuant to 37 CFR 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO/SB/08. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is filed before the mailing date of a first Office Action after the filing of a Request for Continued Examination under 37 CFR 1.114 (37 CFR 1.97(b)(4)).

Application No.: 09/855,532



Docket No.: M4065.0439/P439

In accordance with 37 CFR 1.97(g), the filing of this Information Disclosure Statement shall not be construed to mean that a search has been made or that no other material information as defined in 37 CFR 1.56(a) exists. In accordance with 37 CFR 1.97(h), the filing of this Information Disclosure statement shall not be construed to be an admission that any patent, publication or other information referred to therein is "prior art" for this invention unless specifically designated as such.

It is submitted that the Information Disclosure Statement is in compliance with 37 CFR 1.98 and the Examiner is respectfully requested to consider the listed references.

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0439/P439.

Dated: March 22, 2006

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

Gabriela I. Coman

Registration No.: 50,515

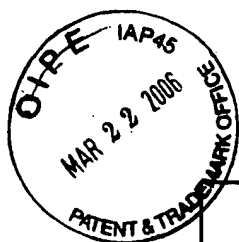
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Attorneys for Applicant



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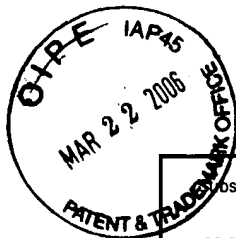
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				Application Number	09/855,532-Conf. #9772
				Filing Date	May 16, 2001
				First Named Inventor	Joseph E. Geusic
				Art Unit	2828
				Examiner Name	A. Rodriguez
				Attorney Docket Number	M4065.0439/P439
Sheet	1	of	10		

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Examiner Initials*	Cite No. 1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code 2 (if known)			
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				Art Unit	2828
				Examiner Name	A. Rodriguez
				Attorney Docket Number	M4065.0439/P439
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	AV1	6,016,000	01-2000	Moslehi	
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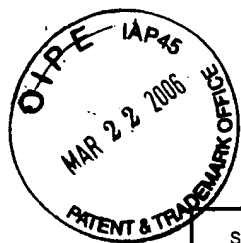
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				Art Unit	2828
				Examiner Name	A. Rodriguez
Sheet	3	of	10	Attorney Docket Number	M4065.0439/P439

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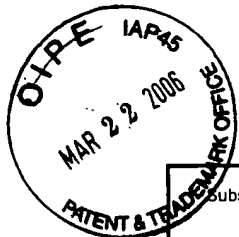
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				Art Unit	2828
				Examiner Name	A. Rodriguez
				Attorney Docket Number	M4065.0439/P439
Sheet	4	of	10		

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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				
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Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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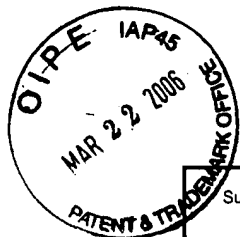
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			Examiner Name	A. Rodriguez	
Sheet	5	of	10	Attorney Docket Number	M4065.0439/P439

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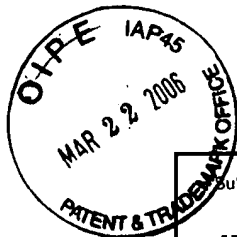
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			Application Number	09/855,532-Conf. #9772	
			Filing Date	May 16, 2001	
			First Named Inventor	Joseph E. Geusic	
			Art Unit	2828	
			Examiner Name	A. Rodriguez	
Sheet	6	of	10	Attorney Docket Number	M4065.0439/P439

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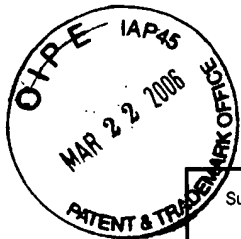
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				Examiner Name	A. Rodriguez
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	CS1	HADDAD, H.; Forbes, L., Electrical activity of bulk stacking faults in silicon, Materials Letters, 7(3) Sep 1988, 99-101.	
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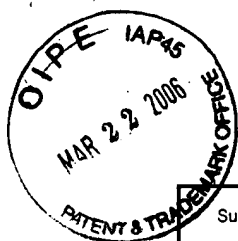
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			Examiner Name	A. Rodriguez	
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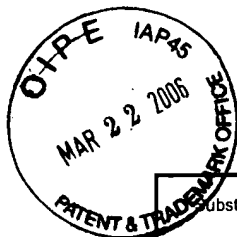
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			Art Unit	2828	
			Examiner Name	A. Rodriguez	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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